

# MMBTA63LT1G, MMBTA64LT1G, SMMBTA64LT1G

## Darlington Transistors

### PNP Silicon

#### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CES}$	–30	Vdc
Collector–Base Voltage	$V_{CBO}$	–30	Vdc
Emitter–Base Voltage	$V_{EBO}$	–10	Vdc
Collector Current – Continuous	$I_C$	–500	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	–55 to +150	$^\circ\text{C}$

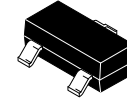
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR–5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

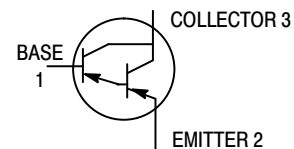


ON Semiconductor®

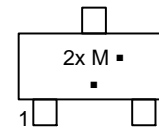
[www.onsemi.com](http://www.onsemi.com)



SOT–23 (TO–236)  
CASE 318  
STYLE 6



#### MARKING DIAGRAM



2x = Device Code  
 x = U for MMBTA63LT1G  
 x = V for MMBTA64LT1G  
 SMMBTA64LT1G  
 M = Date Code\*  
 ■ = Pb–Free Package

(Note: Microdot may be in either location)  
 \*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBTA63LT1G	SOT–23 (Pb–Free)	3,000 / Tape & Reel
MMBTA64LT1G	SOT–23 (Pb–Free)	3,000 / Tape & Reel
SMMBTA64LT1G	SOT–23 (Pb–Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBTA63LT1G, MMBTA64LT1G, SMMBTA64LT1G

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage ( $I_C = -100\ \mu\text{Adc}$ )	$V_{(BR)CEO}$	-30	-	Vdc
Collector Cutoff Current ( $V_{CB} = -30\ \text{Vdc}$ )	$I_{CBO}$	-	-100	nAdc
Emitter Cutoff Current ( $V_{EB} = -10\ \text{Vdc}$ )	$I_{EBO}$	-	-100	nAdc
<b>ON CHARACTERISTICS</b>				
DC Current Gain (Note 3) ( $I_C = -10\ \text{mAdc}$ , $V_{CE} = -5.0\ \text{Vdc}$ ) MMBTA63 ( $I_C = -10\ \text{mAdc}$ , $V_{CE} = -5.0\ \text{Vdc}$ ) MMBTA64, SMMBTA64 ( $I_C = -100\ \text{mAdc}$ , $V_{CE} = -5.0\ \text{Vdc}$ ) MMBTA63 ( $I_C = -100\ \text{mAdc}$ , $V_{CE} = -5.0\ \text{Vdc}$ ) MMBTA64, SMMBTA64	$h_{FE}$			-
		5,000	-	
		10,000	-	
		10,000	-	
		20,000	-	
Collector–Emitter Saturation Voltage ( $I_C = -100\ \text{mAdc}$ , $I_B = -0.1\ \text{mAdc}$ )	$V_{CE(sat)}$	-	-1.5	Vdc
Base – Emitter On Voltage ( $I_C = -100\ \text{mAdc}$ , $V_{CE} = -5.0\ \text{Vdc}$ )	$V_{BE(on)}$	-	-2.0	Vdc
<b>SMALL– SIGNAL CHARACTERISTICS</b>				
Current–Gain – Bandwidth Product ( $I_C = -10\ \text{mAdc}$ , $V_{CE} = -5.0\ \text{Vdc}$ , $f = 100\ \text{MHz}$ )	$f_T$	125	-	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

# MMBTA63LT1G, MMBTA64LT1G, SMMBTA64LT1G

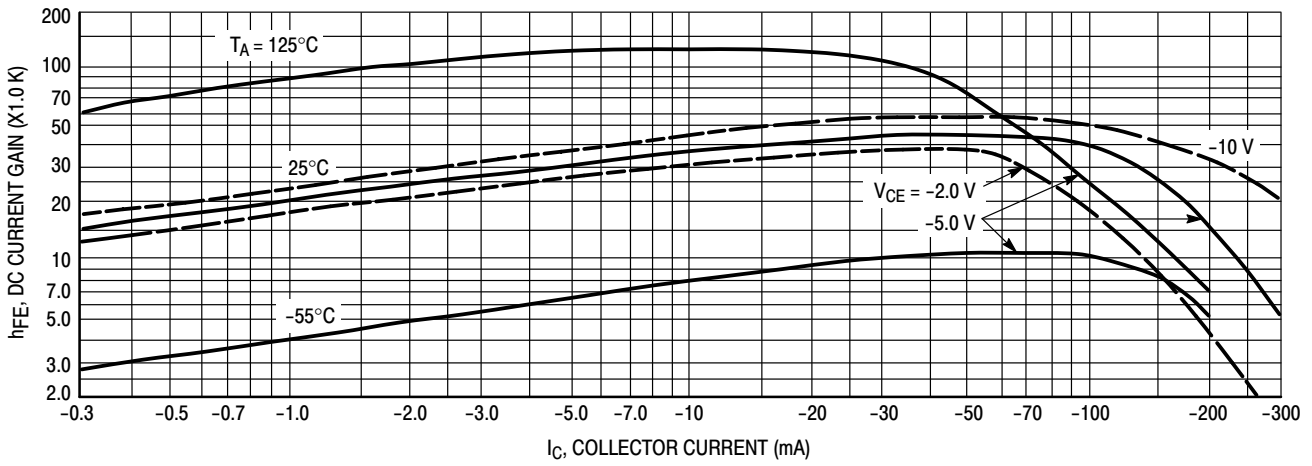


Figure 1. DC Current Gain

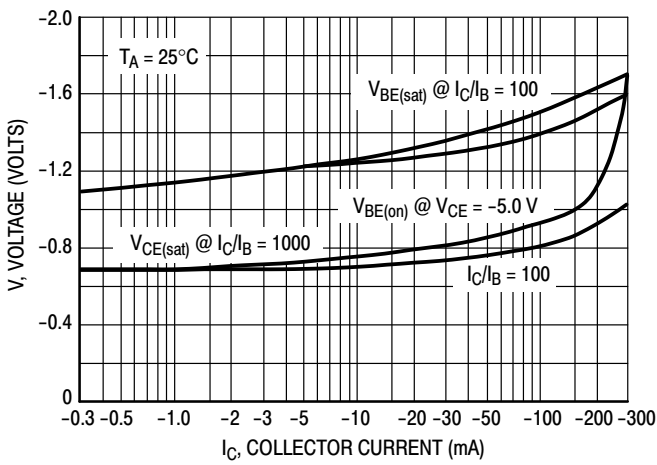


Figure 3. "On" Voltage

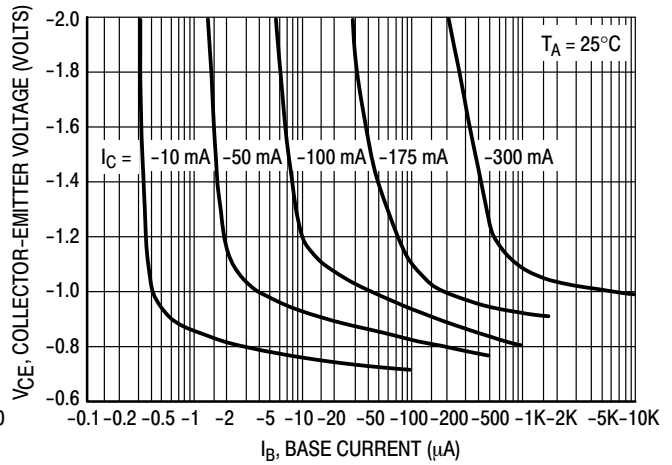


Figure 2. Collector Saturation Region

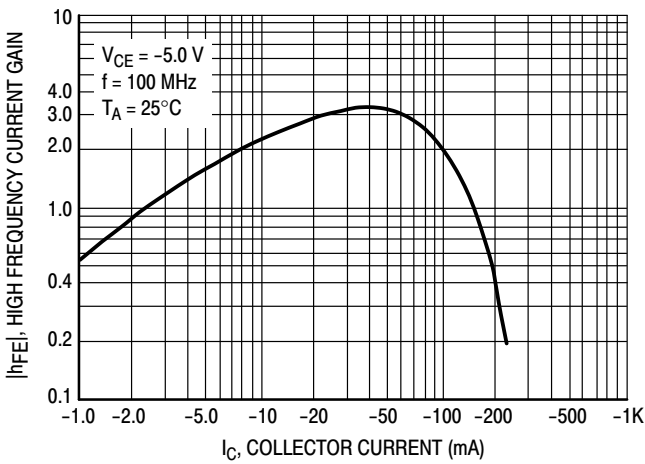


Figure 4. High Frequency Current Gain

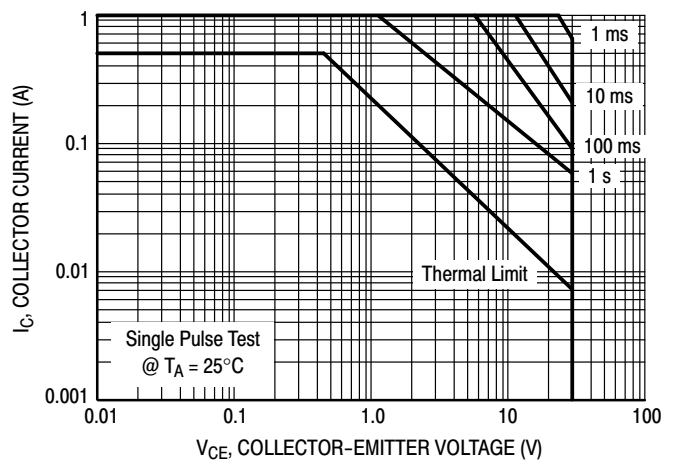


Figure 5. Safe Operating Area

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



**SOT-23 (TO-236)**  
**CASE 318-08**  
**ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**RECOMMENDED SOLDERING FOOTPRINT**



**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- |                                                             |                                                             |                                                             |                                                            |
|-------------------------------------------------------------|-------------------------------------------------------------|-------------------------------------------------------------|------------------------------------------------------------|
| STYLE 1 THRU 5:<br>CANCELLED                                | STYLE 6:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR       | STYLE 7:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR       | STYLE 8:<br>PIN 1. ANODE<br>2. NO CONNECTION<br>3. CATHODE |
| STYLE 9:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE          | STYLE 10:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE           | STYLE 11:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 12:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE      |
| STYLE 13:<br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE           | STYLE 14:<br>PIN 1. CATHODE<br>2. GATE<br>3. ANODE          | STYLE 15:<br>PIN 1. GATE<br>2. CATHODE<br>3. ANODE          | STYLE 16:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE      |
| STYLE 17:<br>PIN 1. NO CONNECTION<br>2. ANODE<br>3. CATHODE | STYLE 18:<br>PIN 1. NO CONNECTION<br>2. CATHODE<br>3. ANODE | STYLE 19:<br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE-ANODE | STYLE 20:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE         |
| STYLE 21:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN           | STYLE 22:<br>PIN 1. RETURN<br>2. OUTPUT<br>3. INPUT         | STYLE 23:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE         | STYLE 24:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE          |
| STYLE 25:<br>PIN 1. ANODE<br>2. CATHODE<br>3. GATE          | STYLE 26:<br>PIN 1. CATHODE<br>2. ANODE<br>3. NO CONNECTION | STYLE 27:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE     | STYLE 28:<br>PIN 1. ANODE<br>2. ANODE<br>3. ANODE          |

<b>DOCUMENT NUMBER:</b>	<b>98ASB42226B</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>SOT-23 (TO-236)</b>	<b>PAGE 1 OF 1</b>

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.